



**RESPONSE UNDER 37 C.F.R. § 1.116  
EXPEDITED PROCEDURE  
EXAMINING GROUP 2881**

**PATENT**  
**DKT. NO.: 29273/502**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

APPLICANTS : Hajime KAWANO, et al.

SERIAL NO. : 09/315,988

FILED : May 21, 1999

## FOR : ELECTRON BEAM LITHOGRAPHY SYSTEM

GROUP ART . . . . . 2881

EXAMINER : Kalimah Fernandez

COMMISSIONER FOR PATENTS

CONVERSATION

Alexandria, VA 22313-1450

## AMENDMENT

Sir.

In response to the office action dated January 29, 2003, the due date being extended by the attached Petition for Extension of Time, please amend the above-identified application as follows:

## IN THE CLAIMS

Please amend claim 1 as follows:

1. (Twice) An electron beam lithography system comprising:
  - exposure map creating means which, based on positional relations between meshes dividing a region to be rendered by an electron beam on the one hand and shots to be rendered by said electron beam on the other hand, creates an exposure map by calculating an area density from a shot area included in each of said meshes; and
  - proximity effect correcting means for correcting a level of exposure for each of said shots by referencing said exposure map so that each shot is exposed at the corrected level;